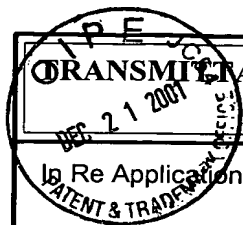


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<b>TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT</b> (Under 37 CFR 1.97(b) or 1.97(c))		Docket No. 11471-US	
In Re Application Of: Luc Ouellet et al.			
Serial No. 09/867,662	Filing Date 05/31/01	Examiner	Group Art Unit 1762
Title: METHOD OF DEPOSITING OPTICAL FILMS			
<p style="text-align: center;">Address to: Assistant Commissioner for Patents Washington, D.C. 20231</p> <p style="text-align: center;"><b>37 CFR 1.97(b)</b></p> <p>1. <input checked="" type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application; within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or, before the mailing date of a first Office Action on the merits, whichever event occurs last.</p> <p style="text-align: center;"><b>37 CFR 1.97(c)</b></p> <p>2. <input type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed after three months of the filing of a national application, or the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or after the mailing date of a first Office Action on the merits, whichever occurred last but before the mailing date of either:</p> <p style="margin-left: 40px;">1. a Final Action under 37 CFR 1.113, or</p> <p style="margin-left: 40px;">2. a Notice of Allowance under 37 CFR 1.311,</p> <p style="margin-left: 40px;">whichever occurs first.</p> <p>Also submitted herewith is:</p> <p><input type="checkbox"/> a certification as specified in 37 CFR 1.97(e);</p> <p style="text-align: center;"><b>OR</b></p> <p><input type="checkbox"/> the fee set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under 37 CFR 1.97(c).</p>			

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**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**  
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.  
11471-US

In Re Application Of: Luc Ouellet et al.

Serial No.  
09/867,662

Filing Date  
05/31/01

Examiner

Group Art Unit  
1762

Title:  
**METHOD OF DEPOSITING OPTICAL FILMS**

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(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

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Dated: December 17, 2001

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APPLICANT

Luc OUELLET et al.

FILING DATE

May 31, 2001

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## U.S. PATENT DOCUMENTS

*Exam. Inti.	Document Number	Date	Name	Class	Sub Class	Filing Date if Appropriate

## FOREIGN PATENT DOCUMENTS

Document Number	Date	Country	Class	Sub Class	Translation	
					Yes	No

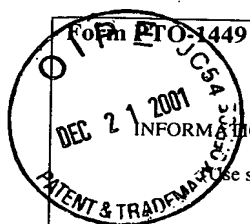
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APPLICANT

Luc OUELLET et al.

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**U.S. PATENT DOCUMENTS**

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**FOREIGN PATENT DOCUMENTS**

Document Number	Date	Country	Class	Sub Class	Translation	
					Yes	No

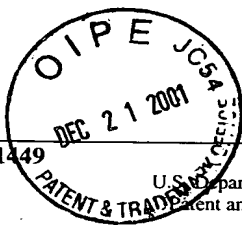
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				APPLICANT Luc OUELLET et al.			
				FILING DATE May 31, 2001		GROUP	
<b>U.S. PATENT DOCUMENTS</b>							
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<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Sub Class	Translation Yes No
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